



TAYCHIPST

HIGH EFFICIENCY RECTIFIER

RU3YX(Z) THRU RU3C(Z)

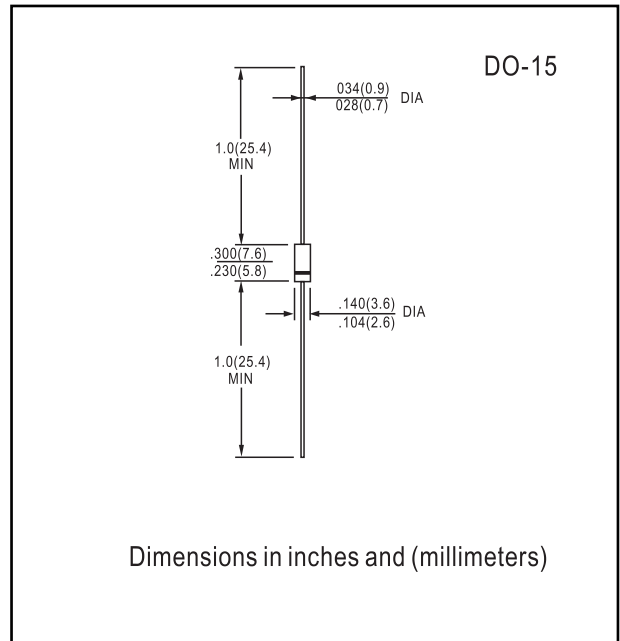
100V-1000V 1.1A-2.0A

FEATURES

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ Easily cleaned with freon, alcohol, Isopropand and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case: JEDEC DO-15, molded plastic
- ◇ Terminals: Axial leads, solderable per MIL-STD-202, Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.024 ounces, 0.68 grams
- ◇ Mounting: Any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

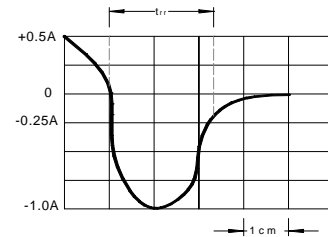
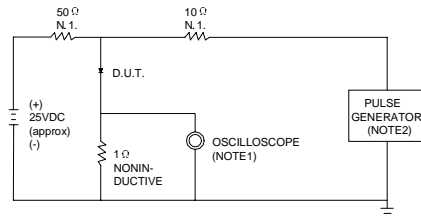
		RU3YX	RU3	RU3A	RU3B	RU3C	UNITS
Maximum peak repetitive reverse voltage	V_{RRM}	100	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	70	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	100	400	600	800	1000	V
Maximum average forward rectified current 9.5mm lead length, @ $T_A=75^\circ C$	$I_{F(AV)}$	2.0	1.5		1.1	1.5	A
Peak forward surge current 10ms single half-sine-wave superimposed on rated load @ $T_J=125^\circ C$	I_{FSM}	50.0	20.0				A
Maximum instantaneous forward voltage @ $I_F=I_{F(AV)}$	V_F	0.95	1.5		2.5		V
Maximum reverse current @ $T_A=25^\circ C$ at rated DC blocking voltage @ $T_A=100^\circ C$	I_R	10.0				μA	
		300.0	400.0				
Maximum reverse recovery time (Note1)	t_{rr}	50	100				ns
Typical junction capacitance (Note2)	C_J	50		30			pF
Typical thermal resistance (Note3)	$R_{\theta JL}$	12					$^\circ C/W$
Operating junction temperature range	T_J	- 55 ----- + 150					$^\circ C$
Storage temperature range	T_{STG}	- 55 ----- + 150					$^\circ C$

NOTE: 1. Measured with $I_F=0.5A$, $I_R=1A$, $I_{rr}=0.25A$
 2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
 3. Thermal resistance junction to ambient.



RATINGS AND CHARACTERISTIC CURVES RU3YX(Z) THRU RU3C(Z)

FIG.1 – TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES: 1. RISE TIME = 7ns MAX INPUT IMPEDANCE = 1MΩ, 22pF.
2. RISE TIME = 10ns MAX SOURCE IMPEDANCE = 50 Ω.

SET TIME BASE FOR 10/20 ns/cm

FIG.2 – TYPICAL FORWARD CHARACTERISTIC

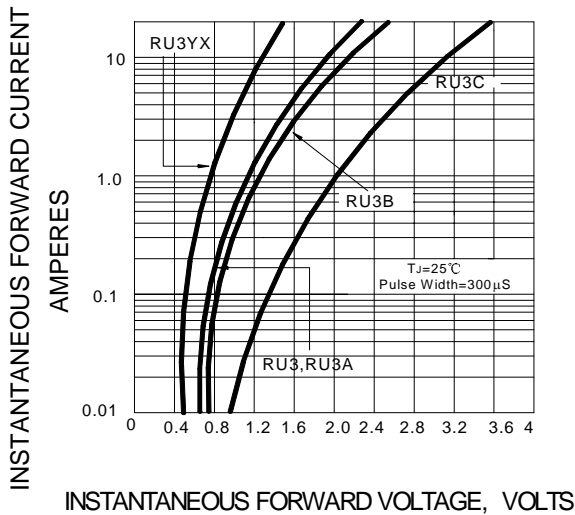


FIG.3 – FORWARD DERATING CURVE

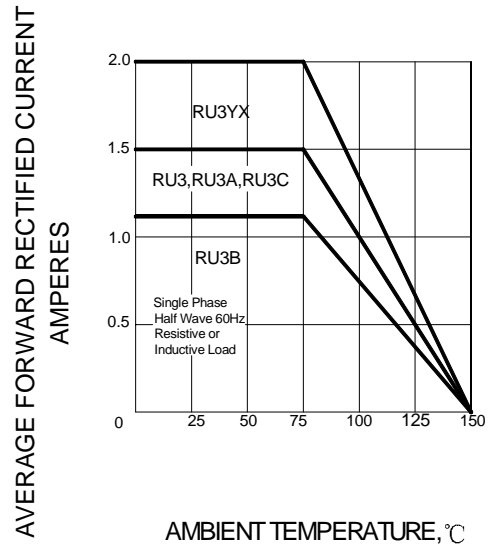


FIG.4 – PEAK FORWARD SURGE CURRENT

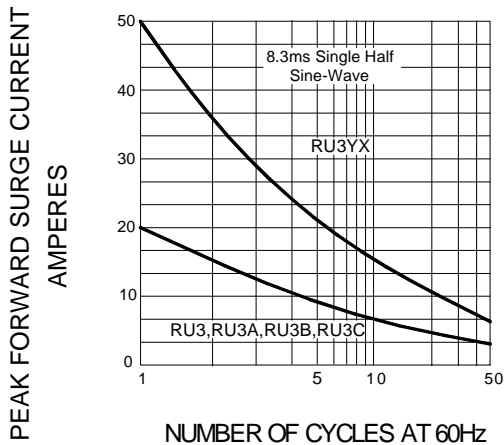


FIG.5 – TYPICAL JUNCTION CAPACITANCE

